

RJK1021DPN

N-Channel Power MOSFET High-Speed Switching Use

REJ03G1628-0100 Rev.1.00 Apr 02, 2008

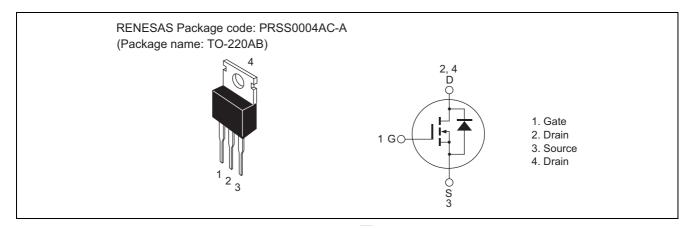
Features

• V_{DSS}: 100 V

• $R_{DS(on)}$: 20 m Ω (Max)

• I_D: 70 A

Outline



Application

• Motor control, Solenoid control, DC-DC converter, etc.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	100	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I _D	70	А
Drain peak current	I _{D (pulse)}	140	А
Body-drain diode reverse drain current	I _{DR}	70	А
Body-drain diode reverse drain peak current	I _{DR (pulse)}	140	А
Avalanche current	I _{AP} Note2	35	А
Channel dissipation	Pch Note1	100	W
Channel to case thermal impedance	θch-c	1.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Value at Tc = 25°C

2. STch = 25°C, Tch \leq 150°C, L = 100 μH

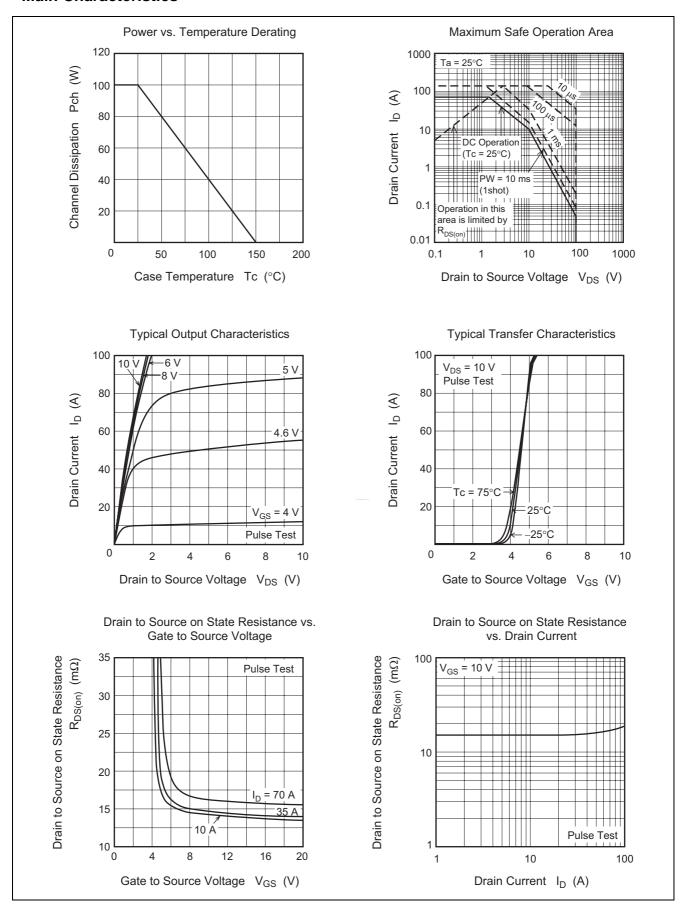
Electrical Characteristics

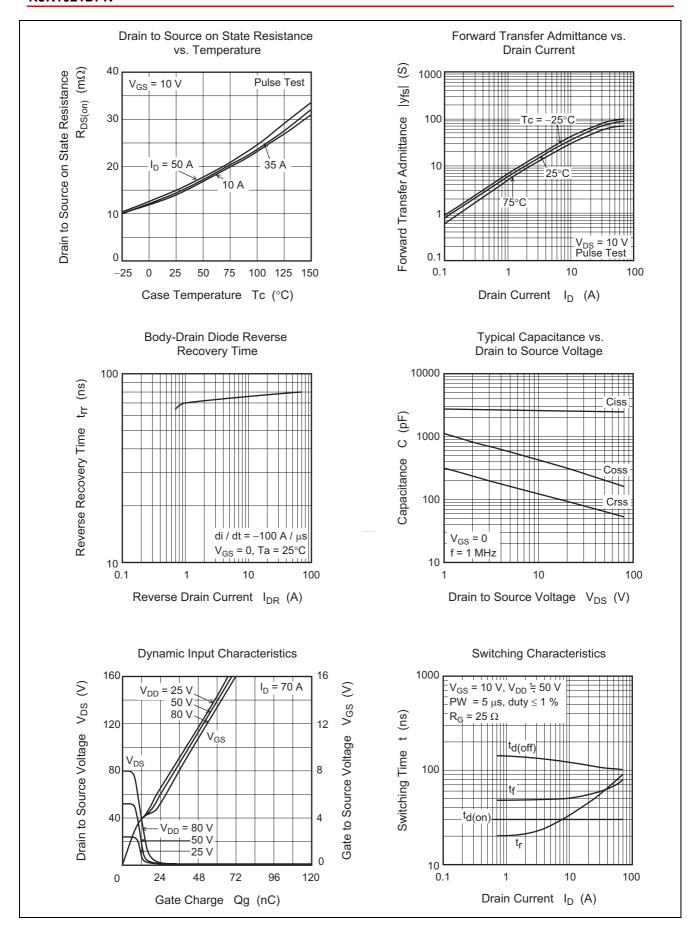
 $(Ta = 25^{\circ}C)$

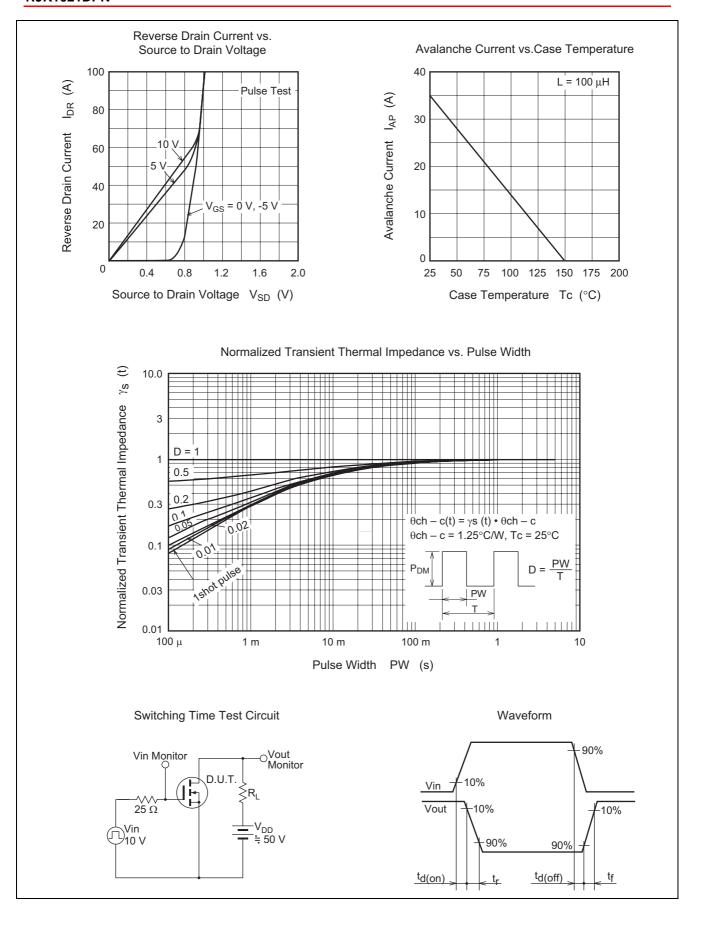
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	100	μΑ	$V_{DS} = 100 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state voltage	V _{DS(on)}	_	0.56	0.70	V	$I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state	R _{DS(on)}	_	16	20	mΩ	$I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
resistance						
Input capacitance	Ciss		2600	_	pF	V _{DS} = 10 V
Output capacitance	Coss		430	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	160	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	30	_	ns	V _{DD} = 50 V
Rise time	t _r		70	_	ns	I _D = 35 A
Turn-off delay time	t _{d(off)}		110	_	ns	V _{GS} = 10 V
Fall time	t _f		65	_	ns	$R_G = 25 \Omega$
Body-drain diode forward voltage	V_{DF}	_	0.9	1.5	V	I _F = 35 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	_	80	_	ns	I _F = 70 A, V _{GS} = 0
						di _F /dt = 100 A/μs

Notes: 3. Pulse test

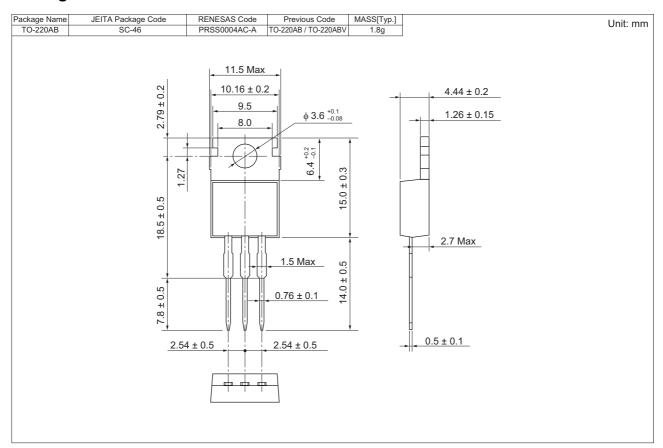
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK1021DPN-00-00	500 pcs	Box (Sack)

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